

# Low-Temperature Annealing of Polycrystalline $\text{Si}_{1-x}\text{Ge}_x$ After Dopant Implantation

Zhonghe Jin, Bhat A. Gururaj, Milton W. Y. Yeung, Hoi Sing Kwok, *Senior Member, IEEE*, and Man Wong

**Abstract**—Hall effect measurement was employed to study the isothermal annealing of boron or phosphorus implanted polycrystalline  $\text{Si}_{1-x}\text{Ge}_x$  thin films, with  $x$  varying from 0.3–0.55. X-ray diffraction and cross-sectional transmission electron microscopy were used to study the crystal structure, whereas X-ray photoelectron spectroscopy was used to determine the film composition and the chemical bonding states of the elements. In low-temperature ( $\leq 600^\circ\text{C}$ ) annealing, the conductivity, the dopant activation, and the Hall effect mobility decreased during extended annealing. The effective activation of phosphorus was less than 20% and decreased with increasing Ge content. Boron activation could reach above 70%. It was also found that  $\text{Si}_{1-x}\text{Ge}_x$  could be oxidized at  $600^\circ\text{C}$  in a conventional furnace even with  $\text{N}_2$  protection, especially for phosphorus doped films with high Ge content. Consequently, a low-temperature  $\text{SiO}_2$  capping layer is necessary during extended annealing.

## I. INTRODUCTION

**P**OLYCRYSTALLINE  $\text{Si}_{1-x}\text{Ge}_x$  (poly-SiGe) is an attractive alternative to polycrystalline silicon (poly-Si) in silicon integrated circuits [1]. The advantages of poly-SiGe over poly-Si include low process temperature and high mobility. For undoped  $\text{Si}_{1-x}\text{Ge}_x$ , crystallization can occur at a much lower temperature or for a shorter annealing time than for silicon [2]. Some authors [3], [4] also pointed out that the boron activation in poly-SiGe was much easier than in poly-Si. The activation behavior of doped poly-SiGe as a function of the annealing conditions has been studied [4]. However, the explanations for some phenomena are still far from clear, such as why the resistivity of the phosphorus doped poly-SiGe increases rapidly with increasing  $x$  when  $x > 0.5$  [4], and how and why the Hall effect mobility and the carrier concentration depend on the Ge content. Furthermore, it is still not clear what temperature-time cycles are necessary to activate dopants in poly-SiGe, particularly for low-temperature thin-film transistors.

In this paper, we present the results of a study on the low-temperature annealing of implanted poly-SiGe, with  $x$  varying from 0.3–0.55. Hall effect measurements were used

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Z. Jin is with the Department of Electrical and Electronic Engineering, Hong Kong University of Science and Technology, Kowloon, Hong Kong and the Department of Information and Electronic Engineering, Zhejiang University, Hangzhou 310008, China.

B. A. Gururaj, M. W. Y. Yeung, H. S. Kwok, and M. Wong are with the Department of Electrical and Electronic Engineering, Hong Kong University of Science and Technology, Kowloon, Hong Kong (e-mail: eem-wong@usthk.ust.hk).

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TABLE I  
SiGe DEPOSITION CONDITIONS

Sample No.	Deposition temperature ( $^\circ\text{C}$ )	$\text{GeH}_4$ flow rate (sccm)	$\text{SiH}_4$ flow rate (sccm)	Deposition time (min)	SiGe thickness (nm)	Si/Ge composition
49	450	22	70	45	250	0.45/0.55
50	500	10	70	22	200	0.7/0.3
51*	500	10	70	35	300	0.7/0.3
52*	500	10	70	22	200	0.7/0.3
53	450	22	70	45	250	0.45/0.55
54	450	10	70	45	210	0.55/0.45

\* All the samples, except No.51 and 52, were crystallized for 7 hours at  $550^\circ\text{C}$  before ion implantation.

to measure the electrical characteristics of doped poly-SiGe. X-ray diffraction (XRD) and cross-sectional transmission electron microscopy (XTEM) were used to characterize the crystal structure. X-ray photoelectron spectroscopy (XPS) was used to measure the film composition and the chemical bonding states of the elements.

## II. EXPERIMENTAL

Poly-SiGe films were deposited at low pressure (0.3 Torr) by chemical vapor deposition at  $450$  or  $500^\circ\text{C}$  on thermally oxidized (100), p-type, 100-mm Si wafers. The source gases were  $\text{SiH}_4$  and  $\text{GeH}_4$ . The deposition technique has been studied in detail by others [5]. Because of the poor nucleation of SiGe on oxide,  $\text{SiH}_4$  was turned on 30 min earlier than  $\text{GeH}_4$ . Other deposition conditions are shown in Table I. The deposition time listed does not include the 30-min  $\text{SiH}_4$  pretreatment time. At  $500^\circ\text{C}$ , 10 nm of amorphous silicon (a-Si) was deposited during the pretreatment, but no measurable a-Si layer could be deposited at  $450^\circ\text{C}$ . However, we believe some silicon seeds could be formed on the oxide during the 30-min pretreatment at  $450^\circ\text{C}$ , which nevertheless induced SiGe deposition. The thickness of the poly-SiGe thin films was between 200–250 nm, as measured by a surface profiler. To make sure the SiGe thin films were crystallized completely, Samples 49, 50, 53, and 54 were annealed at  $550^\circ\text{C}$  for 7 h in  $\text{N}_2$  immediately following the SiGe deposition. Sample 52 was not crystallized in order to find out if there was any difference

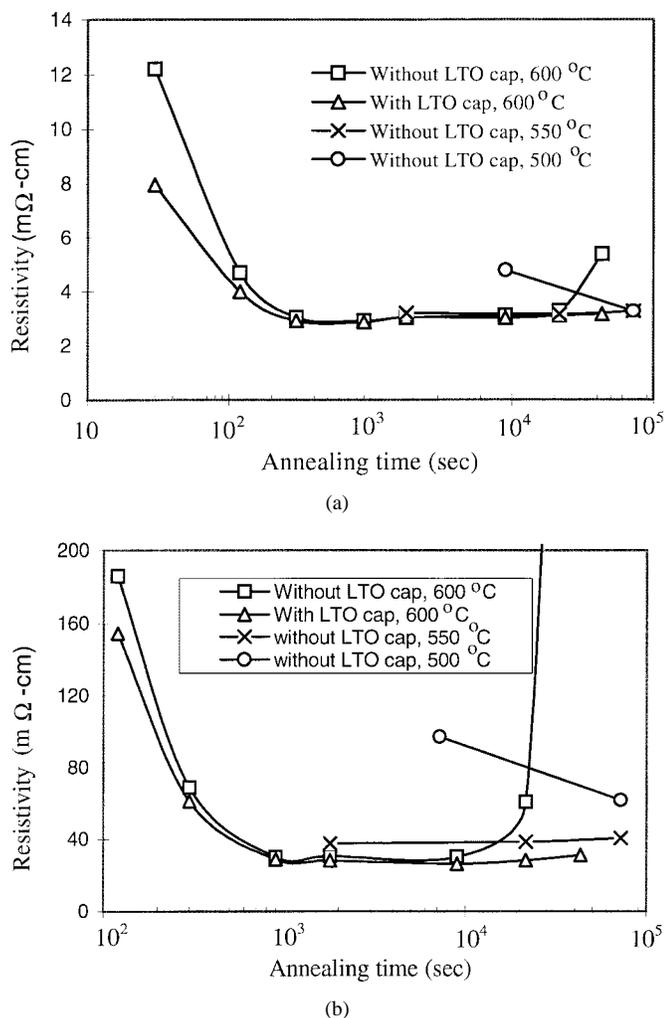


Fig. 1. Resistivity of (a) the p-type and (b) the n-type  $\text{Si}_{0.45}\text{Ge}_{0.55}$  as a function of annealing time.

between the dopant activation behavior of the crystallized and the as-deposited  $\text{SiGe}$ .

Phosphorus or boron was implanted two consecutive times to obtain a smooth concentration profile. For the p-type samples, boron was implanted at 35 keV and a dose of  $2 \times 10^{15} \text{ cm}^{-2}$ , followed by  $\text{BF}_2^+$  at 35 keV and a dose of  $2 \times 10^{15} \text{ cm}^{-2}$ . For the n-type samples, phosphorus was implanted at 80 keV and a dose of  $2 \times 10^{15} \text{ cm}^{-2}$ , followed by the same ion at 40 keV and a dose of  $2 \times 10^{15} \text{ cm}^{-2}$ . All the implanted wafers were cut into  $1 \times 1 \text{ cm}^2$  square pieces. Some of them were capped with 100-nm low-temperature oxide (LTO) deposited at  $425^\circ \text{C}$ . The samples were annealed at different temperatures from  $500\text{--}600^\circ \text{C}$ . Annealing time was from 30 s to 20 h. The 30-s to 5-min anneals were done in a rapid thermal annealing (RTA) reactor, whereas the 15-min to 20-h anneals were done in a conventional furnace. All the anneals were done in an  $\text{N}_2$  ambient evaporated from a liquid nitrogen source. The purity of the liquid nitrogen is above 99.99%. However, since the tube is not completely sealed at the loading end, oxygen, together with the laboratory air, can diffuse into the tube to change the purity of nitrogen in the tube.

After annealing, all the samples were measured in a Hall effect measurement system to estimate the sheet resistance,

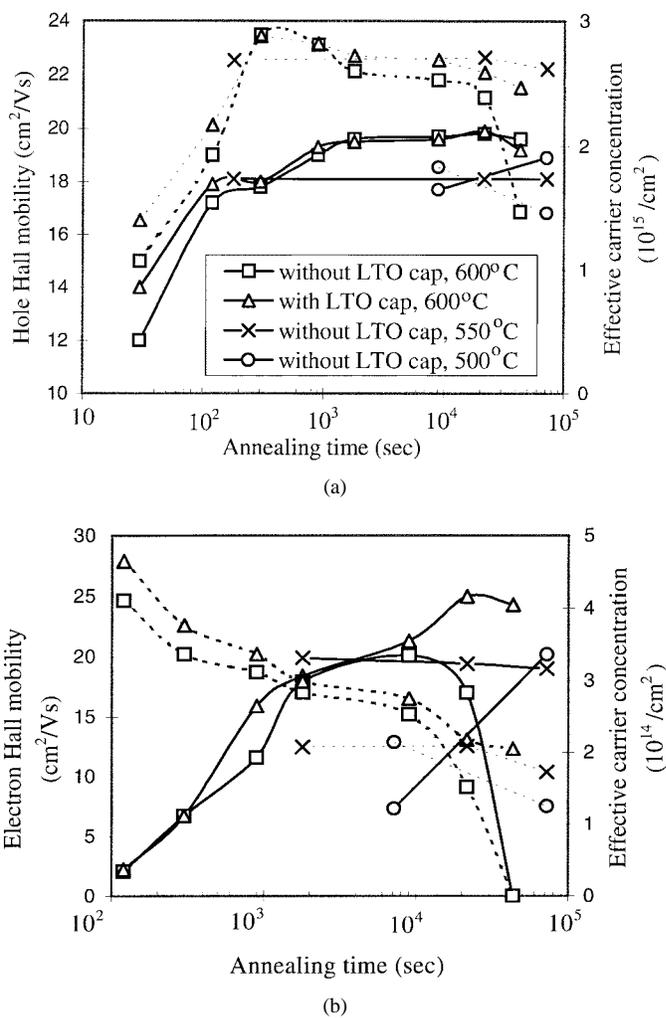


Fig. 2. Hall effect mobility and the effective dopant activation of (a) the p-type and (b) the n-type type  $\text{Si}_{0.45}\text{Ge}_{0.55}$  as functions of annealing time. In both figures, the solid lines are for Hall effect mobility and the dotted lines are for effective dopant activation.

the Hall effect mobility, and the carrier concentration. Some of the samples were analyzed by XRD and XPS. XTEM analysis was done for microstructural analysis.

### III. RESULTS

The resistivity of the p-type and the n-type  $\text{Si}_{0.45}\text{Ge}_{0.55}$  films as a function of the annealing time at different temperatures is summarized in Fig. 1. The behavior is very similar between the n- and the p-type samples, although the resistivity of the n-type samples is always higher than that of the p-type samples. For the samples annealed at  $600^\circ \text{C}$ , the resistivity first decreased quickly with annealing time and then increased gradually on further annealing. For the boron-doped samples, resistivity as low as  $3 \text{ m}\Omega\text{-cm}$  could be obtained after 5 min of annealing at  $600^\circ \text{C}$ . For the phosphorus-doped samples, the lowest resistivity of about  $30 \text{ m}\Omega\text{-cm}$  was obtained after 15 min of annealing at  $600^\circ \text{C}$ . The behavior of the samples with and without the LTO caps was similar for annealing time less than 6 h at  $600^\circ \text{C}$ . Beyond 6 h, the resistivity of the samples without the LTO caps increased more quickly than that of the samples with the LTO caps, especially for the n-type samples.

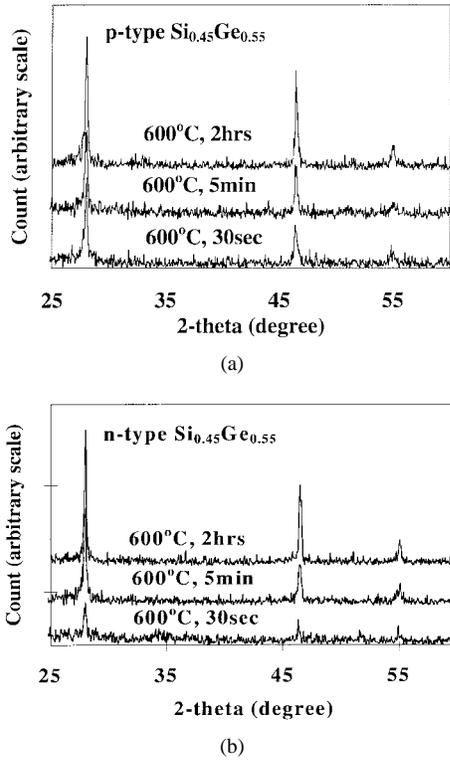


Fig. 3. XRD results of (a) the p-type and (b) the n-type type  $\text{Si}_{0.45}\text{Ge}_{0.55}$  after annealed for 30 s, 5 min, and 2 h at  $600^\circ\text{C}$ .

After 12 h of annealing at  $600^\circ\text{C}$ , the resistivity of the n-type samples without the LTO caps became too large to be measurable in the Hall effect measurement system.

The Hall effect mobility and the effective dopant activation of the p-type and the n-type  $\text{Si}_{0.45}\text{Ge}_{0.55}$  films as functions of annealing time at different temperatures are summarized in Fig. 2. Comparing Figs. 1 and 2, we can see that for the p-type samples, the decrease of the resistivity with annealing time during the first 5 min of annealing was due to both increases in the mobility and in the effective dopant activation. However, for the n-type samples, the decrease in the resistivity was due mainly to the mobility increase during the first 15 min of annealing. Effective phosphorus activation decreased monotonically with the annealing time in all the experiments. After 5 min of annealing, both the conductivity and the effective dopant activation of the p-type samples decreased slowly with the annealing time. The reason for the decrease in effective dopant activation with annealing time was possibly grain boundary segregation [6], formation of dopant pairs [7], or both. The behavior was similar for the samples with or without the LTO caps when the annealing time was less than 6 h. However, the effective dopant activation of the samples without the LTO caps decreased rapidly with annealing time beyond 6 h. This phenomenon will be further elaborated on later in the paper.

The sheet resistance of the n-type  $\text{Si}_{0.45}\text{Ge}_{0.55}$  after 30 s of annealing at  $600^\circ\text{C}$  was still out of the range of the Hall effect measurement system, whereas the p-type samples had sheet resistance values of lower than  $500\ \Omega/\text{square}$ . This was because the implant damage by phosphorus at 80 keV was more severe

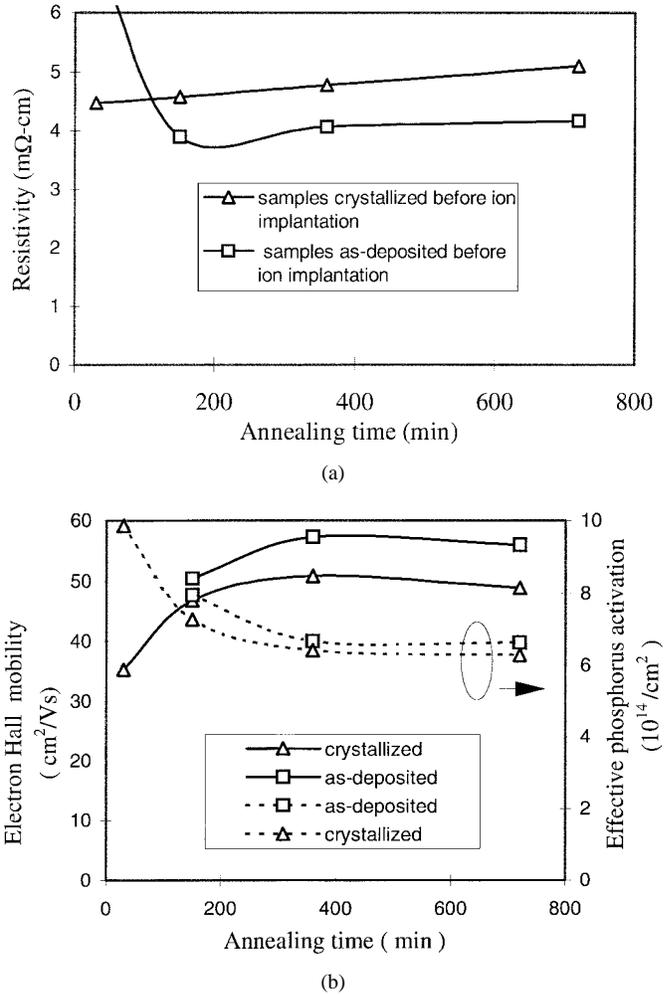


Fig. 4. Influence of crystallization before the phosphorus implantation on the resistivity, the Hall effect mobility, and the phosphorus activation as functions of annealing time after ion implantation. The Ge content is about 30%. All the samples were capped with 100 nm LTO after the ion implantation.

than that of boron at 35 keV. From the XRD results shown in Fig. 3, we can see that although significant crystallization has occurred in the p-type  $\text{Si}_{0.45}\text{Ge}_{0.55}$  samples, the crystallization was far from complete for the n-type  $\text{Si}_{0.45}\text{Ge}_{0.55}$  samples after 30 s of annealing. For the n-type samples, the time needed for significant crystallization was more than 5 min. After 15 min of annealing at  $600^\circ\text{C}$ , the structures became stable for both the n- and the p-type samples, as indicated by the XRD results.

In Fig. 4, the behavior of the crystallized and the as-deposited samples before the ion implantation was compared. The Ge content in the film was about 30%. After 15 min of annealing at  $600^\circ\text{C}$ , the sheet resistance of both kinds of samples was still larger than  $1\ \text{M}\Omega/\text{square}$ , which is the maximum measurable resistance of the equipment. After 30 min of annealing, the resistivity of the samples crystallized before the ion implantation was lower than  $5\ \text{m}\Omega\text{-cm}$ , whereas that of the as-deposited sample before the ion implantation was still out of the measurable range. From the XRD results shown in Fig. 5, we can see that the latter was still amorphous after 30 min of annealing. However, after 150 min of annealing

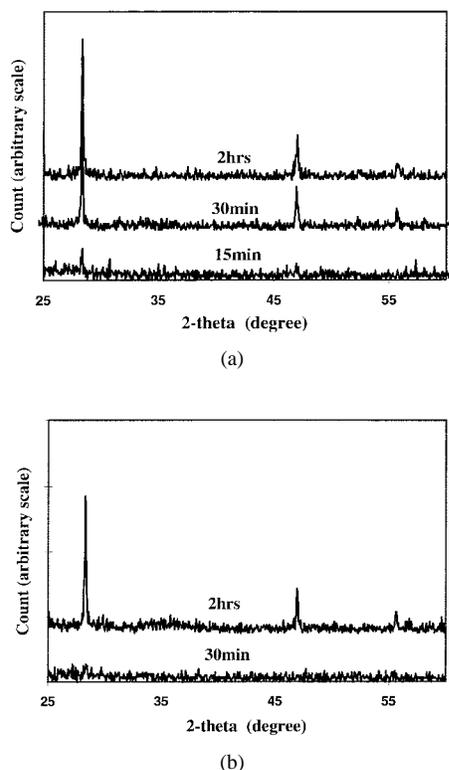


Fig. 5. XRD results of (a) the samples crystallized before the phosphorus implantation and (b) the samples as deposited before the phosphorus implantation. Each XRD trace is labeled by the corresponding implant activation time.

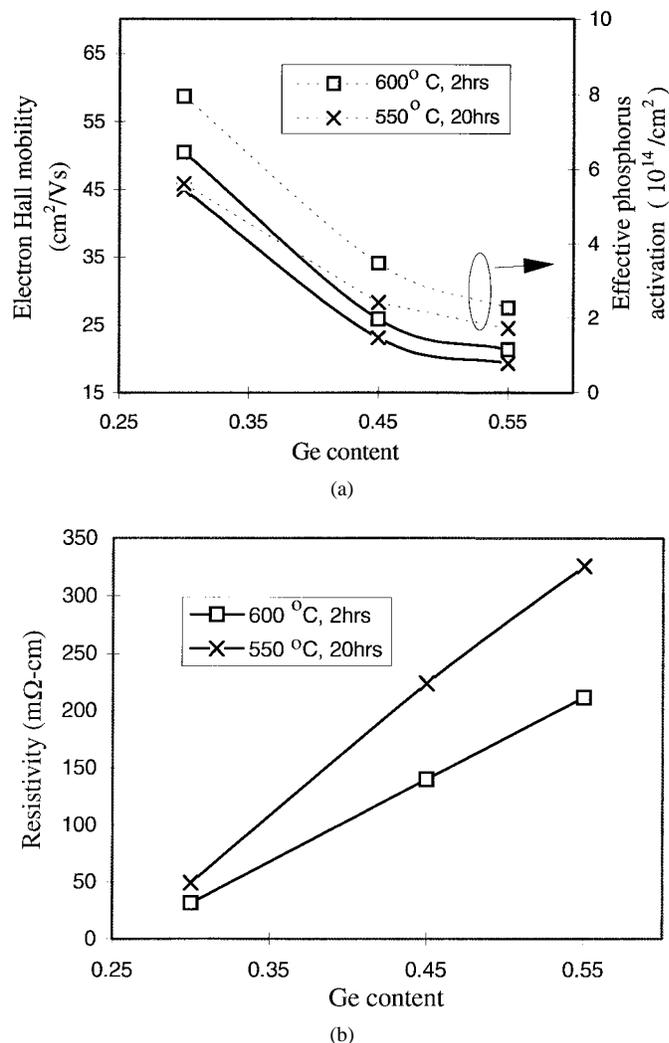


Fig. 7. Resistivity, the Hall effect mobility, and the effective dopant activation of n-type poly-SiGe as functions of the germanium content at different annealing temperatures after ion implantation. In (a), the dotted lines are for the phosphorus activation, and the solid lines are for the Hall effect mobility.



Fig. 6. XTEM micrograph of as-deposited  $\text{Si}_{0.7}\text{Ge}_{0.3}$  film at  $500^\circ\text{C}$  on oxidized silicon. The oxide layer is about 100 nm thick. The SiGe film is about 300 nm thick. We can see the 10-nm a-Si deposited during the 30 min of  $\text{SiH}_4$  pretreatment.

at  $600^\circ\text{C}$ , the conductivity, the Hall effect mobility, and the effective phosphorus activation of the as-deposited samples were higher than those of the crystallized samples.

From the XTEM micrograph (Fig. 6) of the as-deposited sample, we can see that the as-deposited  $\text{Si}_{0.7}\text{Ge}_{0.3}$  was amorphous at the bottom and polycrystalline at the top. After the 80-keV phosphorus implantation, the top 100-nm layer should be amorphized completely by the phosphorus ions. Hence, during the subsequent annealing after implantation, no crystalline seeds existed. Therefore, it would take a longer time to crystallize. For the crystallized samples, no crystalline peak can be detected by XRD after the 80-keV phosphorus implantation. This means the 200-nm films were significantly damaged by the implant, although the calculated implant range should be less than 100 nm. We suspect this could be due to channeling effects in polycrystalline material. It has been noticed that the implant range in crystalline Ge was much larger than that predicted by theory [8]. However, it is still reasonable to consider that some seeds were available near the bottom of the film since the damage at the bottom should not

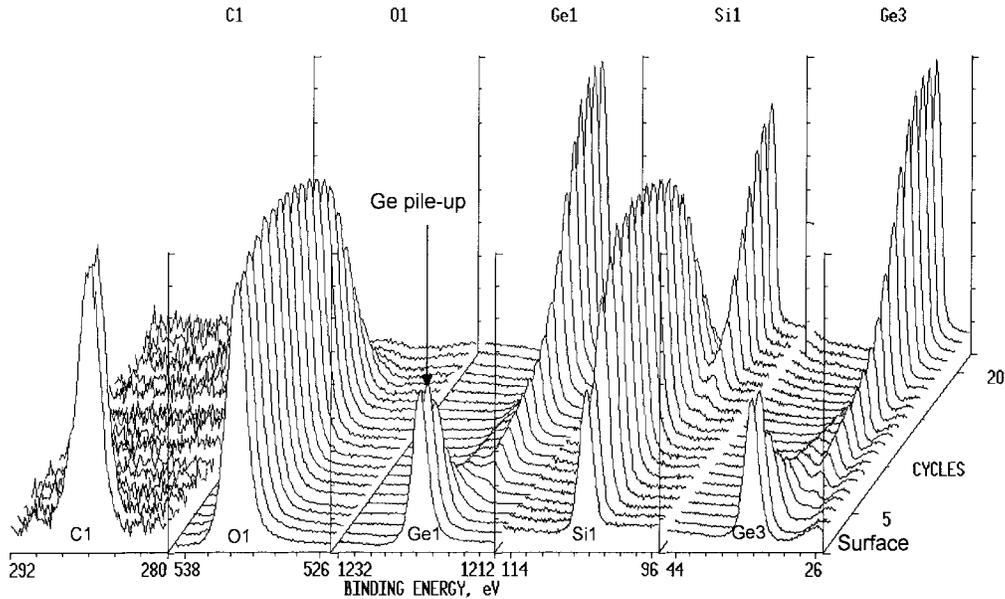


Fig. 8. XPS spectrum of the phosphorus doped  $Si_{0.45}Ge_{0.55}$  without the LTO cap annealed for 6 h at  $600^{\circ}C$  in a conventional furnace with the protection of  $N_2$ . Ar ion was employed to sputter the SiGe film at a rate of about 2 nm/min for the XPS profile. Each cycle, excluding the bottom two in the figure, represents XPS result following 1 min of sputtering. Both of the bottom two cycles represent the XPS results of the film surface.

TABLE II  
ANNEALING TIME NECESSARY IN DIFFERENT TEMPERATURE TO OBTAIN SHEET RESISTANCE LOWER THAN  $5 k\Omega$ . THE FINAL SHEET RESISTANCE OBTAINED AFTER THE ANNEALING SCHEDULE IS ALSO SHOWN

	500°C	550°C	600°C
N-type	> 20 hours	20 hours	30 minutes
$Si_{0.7}Ge_{0.3}$	> $1M\Omega$	246 $\Omega$	179 $\Omega$
N-type	>20 hours	30 minutes	15 minutes
$Si_{0.55}Ge_{0.45}$	> $1M\Omega$	1.8K $\Omega$	559 $\Omega$
N-type	2 hours	30 minutes	5 minutes
$Si_{0.45}Ge_{0.55}$	3.9K $\Omega$	1.5K $\Omega$	2.45K $\Omega$
P-type	2 hours	30 minutes	30 seconds
$Si_{0.45}Ge_{0.55}$	128 $\Omega$	128 $\Omega$	318 $\Omega$

have been as severe as that at the surface. These seeds could shorten the necessary annealing time to recrystallize the film, but the grain size would be smaller than in the film without the seeds. We believe this is why the final conductivity and the Hall effect mobility of the as-deposited samples were higher.

In Fig. 7, the different annealing behavior of the n-type samples with different Ge contents are compared. It can be seen that the conductivity, the Hall effect mobility, and the effective dopant activation of the low Ge content samples were higher than those of the high Ge content samples when the Ge content is in the range from 0.3 to 0.55. This is similar to the results obtained by King *et al.* [4]. In their results, however, the resistivity increased much more rapidly with the Ge content than that which we observed when the Ge content was above 50%. From our experiments, we also noticed that the necessary

annealing time and temperature (Table II) were much less for the high Ge content samples.

IV. DISCUSSION

For the low Ge content SiGe films, Noguchi *et al.* [9] have shown that the resistivity was similar among samples with or without the LTO caps during the annealing. In our experiments, the resistivity of the high Ge content samples changed significantly between those with the LTO caps and those without the LTO caps, especially for the phosphorus doped samples. From Fig. 2, we can see that the carrier concentration and the conductivity decreased with long annealing time at  $600^{\circ}C$  for samples without the LTO caps. After 12 h of annealing, the resistivity of the n-type samples without the LTO caps was out of the measurement range of the equipment. It is suspected that oxidation played an important role here. In a conventional furnace, it is difficult to eliminate trace amounts of oxygen, even in a “pure” nitrogen ambient. SiGe can be oxidized at low temperature [10]. This oxidation could be enhanced by the implanted phosphorus [11]. In addition, out-diffusion of phosphorus would be serious without the LTO caps [6], especially during a lengthy annealing.

An XPS profile (Fig. 8) of  $Si_{0.45}Ge_{0.55}$  without the LTO cap after 6 h of annealing in a conventional furnace at  $600^{\circ}C$  with nitrogen protection clearly showed that the top 30 nm was completely oxidized. It can also be seen that Ge piled up at the surface, similar to the thermal oxidation of SiGe [12]. Further evidence for the 30-nm oxide layer is shown in the XTEM micrograph in Fig. 9. Such thick oxide may indicate that the phosphorus doping could have significantly accelerated the oxidation rate of SiGe.

For the LTO capped n-type samples, the resistivity still increased with the Ge content. This was because of the low effective activation of phosphorus and the low electron

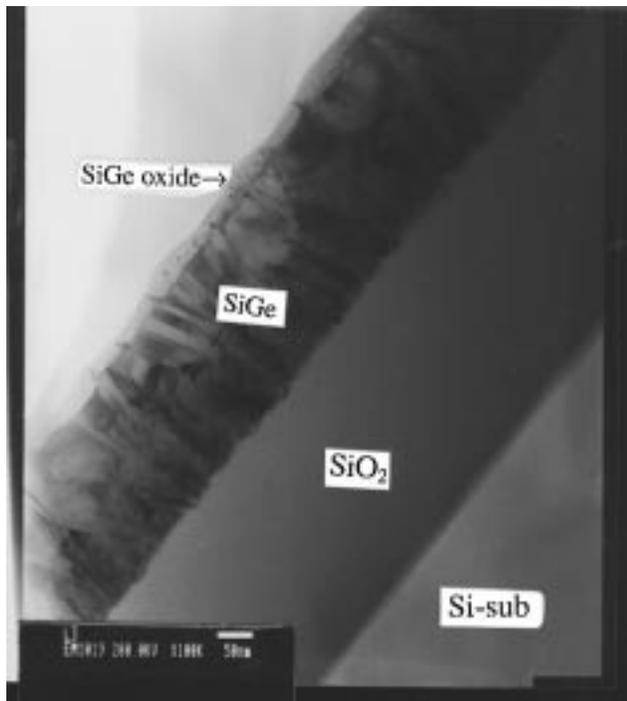


Fig. 9. XTEM micrograph of the phosphorus doped  $\text{Si}_{0.45}\text{Ge}_{0.55}$  without the LTO cap annealed for 6 h at  $600^\circ\text{C}$  in a conventional furnace.

mobility in the samples with high Ge content, as shown in Fig. 7. Herzer and Kalbitzer [8] showed that phosphorus activation in crystalline Ge is as low as 20%, which is much lower than in crystalline Si. The mobility in polycrystalline material was also dependent on the carrier concentration [13]. Therefore, the low activation of phosphorus in high Ge content poly-SiGe was also a reason for the low mobility. The reason for the low effective activation of phosphorus may be the electronic states in the grain boundaries. It has been shown [14] that in poly-Ge grain boundaries, a partially filled band of electronic states exists near the valance band. This band would decrease the effective electron concentration and the electron mobility. The characteristics of the high Ge content poly-SiGe should be similar to those of poly-Ge. In addition, the Ge may enhance the grain boundary segregation of phosphorus. The unactivated phosphorus may exist as phosphorus clusters, especially at the grain boundaries. This would change the material structure and enhance the electron scattering. Hence, the electron mobility would decrease with increasing Ge content.

The boron activation and the hole mobility of high Ge content poly-SiGe were not bad compared with poly-Si. In our experiments, 70% effective activation was obtained. Boron activation also decreased slowly with extended annealing. This may have been due to boron pair formation [7] or grain boundary segregation. The hole mobility of high Ge content poly-SiGe can reach a value  $20\text{ cm}^2/\text{Vs}$ . This could be due to the high boron activation and the smaller density of hole traps in the grain boundaries, contrary to the n-type [14] samples.

It should be pointed out that the necessary annealing time for  $\text{Si}_{0.7}\text{Ge}_{0.3}$  in our experiment is much longer than that used by others [3]. The film thickness here was only 200 nm

and phosphorus implantation energy was 80 keV, whereas in [3], the film thickness was 350–400 nm and the implantation energy was 60 keV. It is suspected that the films in [3] were not completely damaged by the implantation, and therefore, seed layers existed at the bottom of the SiGe layer. This would obviously shorten the recrystallization time.

## V. CONCLUSION

This paper showed that the conductivity, dopant activation, and the Hall effect mobility decreased during extended annealing for the SiGe thin film when the Ge content was in the range of 0.3–0.55. The plausible reason for those decreases may be the grain boundary segregation of dopant during extend annealing. Phosphorus activation and electron mobility decreased with increasing Ge content. One of the possible reasons is the change in the grain boundary trap density with Ge content. Poly-SiGe films, especially those with high Ge content, can be oxidized at low temperature in a conventional furnace, even with “pure” nitrogen protection. This oxidation can be enhanced by heavy phosphorus doping. XPS results showed that Ge piled up at the surface when SiGe was oxidized.

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**Zhonghe Jin** was born in Zhejiang province, China, in January 1970. He received the B.S. degree in 1991 and the M.S. degree in 1994, both from the Department of Information and Electronic Engineering, Zhejiang University.

He joined the Department of Information and Electronic Engineering, Zhejiang University, in 1994, where he was engaged in research and development projects relevant to micromechanical technologies and sensors based on silicon. He has been working as a Visiting Scholar with the Department of Electrical and Electronic Engineering, the Hong Kong University of Science and Technology, since March 1996. He is now researching polycrystalline silicon germanium thin-film transistor technologies. His research interests include micromechanical technologies and sensors, silicon germanium, silicide material properties, and device fabrication.



**Bhat A. Gururaj** was born in New Delhi, India. He received the B.S. (Honors) and M.S. degrees in physics from the University of Delhi and the M.Tech. degree in laser technology from Anna University, Madras, India. He is currently pursuing the Ph.D. degree at the Hong Kong University of Science and Technology.

After receiving the M.Tech. degree, he worked at the National Physical Laboratory, New Delhi, for two years. His current research interests include material processing; characterization, design, and fabrication of thin-film transistors; and laser applications in display devices.



**Milton W. Y. Yeung** received the B.Eng. degree from the Department of Electrical and Electronic Engineering, Hong Kong University of Science and Technology. He is presently pursuing the M.Phil. degree in the same department.

His current research interest is the physics and technology of polycrystalline germanium thin-film transistors.

**Hoi Sing Kwok** (S'73-M'78-SM'84) received the Ph.D. degree from Harvard University, Cambridge, MA, in 1978.

He has been on the faculty at the State University of New York, Buffalo, since 1980. He joined the Hong Kong University of Science and Technology as a Professor in 1993. Currently, he is Director of the Center for Display Research.

Dr. Kwok is a Fellow of the Optical Society of America.



**Man Wong** was born in Beijing, China. He attended primary and secondary schools in Hong Kong and completed his tertiary education in the United States. From 1979 to 1984, he studied at the Massachusetts Institute of Technology, Cambridge, where he received the B.S. and M.S. degrees in electrical engineering. From 1985 to 1988, he was at the Center for Integrated Systems at Stanford University, where he worked on tungsten gate MOS technology and received the Ph.D. degree, also in electrical engineering.

He then joined the Semiconductor Process and Design Center, Texas Instruments, Dallas, and worked on a number of projects, including the modeling and development of the metallization system for the 64 megabit DRAM and the development of dry/vapor cleaning processes. Since September 1992, he has been an Assistant Professor with the Department of Electrical and Electronic Engineering, Hong Kong University of Science and Technology. His current research interests include advanced device fabrication technology, novel device structures and materials, thin-film transistors, display technologies, and micromachines.

Dr. Wong is a member of Tau Beta Pi, Eta Kappa Nu, and Sigma Xi.